

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
S1	49	"361"/\$.ccls. and(decoupling adj capacitor) and power adj layer	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/06 15:56
S2	1	S1 and(insulative adj layer\$1)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/06 15:51
S3	1	S2 and(ground adj layer\$1)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/06 15:52
S4	1	S3 and(lead or connect\$3)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/06 15:52
S5	26	"174"/\$.ccls. and(decoupling adj capacitor) and power adj layer	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/06 16:01
S6	42	semiconductor adj device and insulat\$3 adj body and semiconductor adj die	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/06 16:06
S7	42	S6 and(insulat\$3 adj body)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/06 16:04
S8	0	S7 and(power adj layer\$1 and ground adj layer\$1)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/06 16:03

S9	1709	semiconductor adj device.ti. and semiconductor adj die	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/06 16:07
S10	15	S9 and(power adj layer\$1 or vcc) and(ground adj layer\$1 or vss)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/06 16:35
S11	4936	semiconductor adj die and circuit adj board	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/06 16:35
S12	31	S11 and(insulat\$3 adj body)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/06 16:36
S13	29	S12 and(pin\$1)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/07 10:17
S14	1251	praseodymium adj oxide	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/07 10:18
S15	27	S14 and(diffusion adj barrier)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/07 10:19
S16	15	S15 and electrode\$1	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/07 10:41

S17	19	semiconductor same capacitor and S14	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/07 10:45
S18	47	semiconductor adj device and S14	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/07 10:55
S19	86	capacitor and S14	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/07 13:27
S20	7	S19 and(intermediate adj layer)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/07 10:56
S21	4	S20 and(barrier)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/07 10:56
S22	1230	semiconductor same capacitor same electrode same dielectric same barrier	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/07 13:28
S23	618	"438"/\$.ccls. and (semiconductor same capacitor same electrode same dielectric same barrier)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/07 13:28
S24	69	"361"/\$.ccls. and (semiconductor same capacitor same electrode same dielectric same barrier)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/07 13:30

S25	1251	praseodymium adj oxide	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/07 13:53
S26	0	S24 and praseodymium adj oxide	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/07 13:29
S27	1	S22 and S25	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/07 13:29
S28	0	S23 and S25	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/07 13:29
S29	98318	intermediate adj layer	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/07 13:30
S30	72	S24 and intermediate adj layer	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/07 13:30
S31	3	S24 and intermediate adj layer	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/07 13:31
S32	17	S23 and intermediate adj layer	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/07 13:38

S33	32	S22 and intermediate adj layer	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/07 13:38
S34	146	praseodymium adj oxide SAME DIELECTRIC	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/07 14:10
S35	46	S34 and capacitor	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/08 08:36
S36	86	capacitor and(praseodymium adj oxide)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/08 08:37
S37	8	S36 and(oxynitride)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/08 08:40
S38	7	S36 and(intermediate adj layer)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/08 08:44
S39	203	(intermediate adj layer same oxynitride)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/08 08:44
S40	82	S39 and(electrode\$1)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/08 08:44

S41	50	S40 and(barrier)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/08 08:45
S42	39	S41 and(dielectric)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/08 08:45
S43	28	S42 and(capacitor)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/08 08:54
S44	50509	field adj effect adj transistor same semiconductor	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/08 08:55
S45	114	field adj effect adj transistor same semiconductor adj capacitor	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/08 08:55
S46	109	S45 and(substrate)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/08 08:55
S47	82	S46 and(dielectric)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/08 08:55
S48	16	S47 and(barrier)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/08 08:57

S49	4	S48 and(intermediate)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/08 09:00
S50	8	S47 and(intermediate)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/08 09:01
S51	1	S47 and(oxynitride)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/08 09:01
S52	422	S44 and(oxynitride adj layer)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/08 09:02
S53	283	S52 and(dielectric adj layer)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/08 09:02
S54	183	S53 and(electrode\$1)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/08 09:03
S55	181	S54 and(substrate)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/08 09:03
S56	72	S55 and(ratio)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/08 09:03

S57	71	S56 and(thickness)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/08 09:05
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